Ordering number : EN5300A

N-Channel Silicon MOSFET

2SK2316



Ultrahigh-Speed Switching Applications

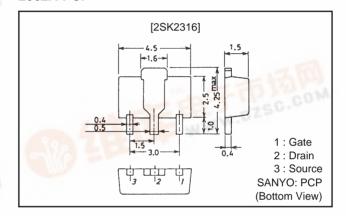
Features

- Low ON resistance.
- Ultrahigh-speed switching.
- Low-voltage drive (2.5V drive).

Package Dimensions www.pzgc.com

unit: mm

2062A-PCP



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		2	Α
Drain Current (Pulse)	IDP	PW≤10µd, duty cycle≤1%	8	Α
Allowable Power Dissipation	PD	Mounted on ceramic board (250mm ² ×0.8mm)	1.5	W
	- 5	Tc=25°C	3.5	W
Channel Temperature	Tch	C.C.O.Se	150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
D-S Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	20	Larry N	C.Dr.	V
G-S Breakdown Voltage	V(BR)GSS	I _G =±100μA, V _D S=0	±10	4		V
Zero-Gate Voltage	IDSS	V _{DS} =16V, V _{GS} =0			100	μΑ
Drain Current		Dha an				
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.5		1.5	V
Forward Transfer Admittance	lyfs	V _{DS} =10V, I _D =1A	1.8	2.8		S
Static Drain-to-Source	RDS(on)	I _D =1A, V _G S=4V		140	200	mΩ
ON-State Resistance	RDS(on)	I _D =1A, V _{GS} =2.5V		200	320	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		170		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		145		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		50		pF

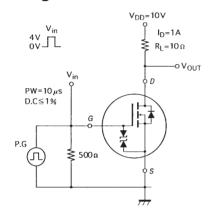
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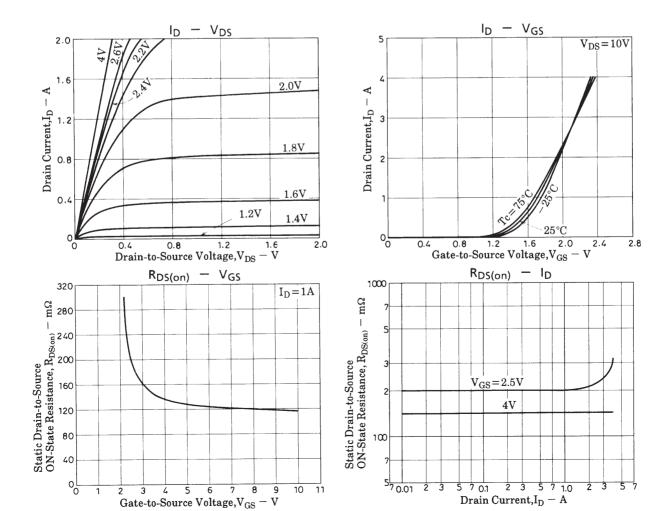
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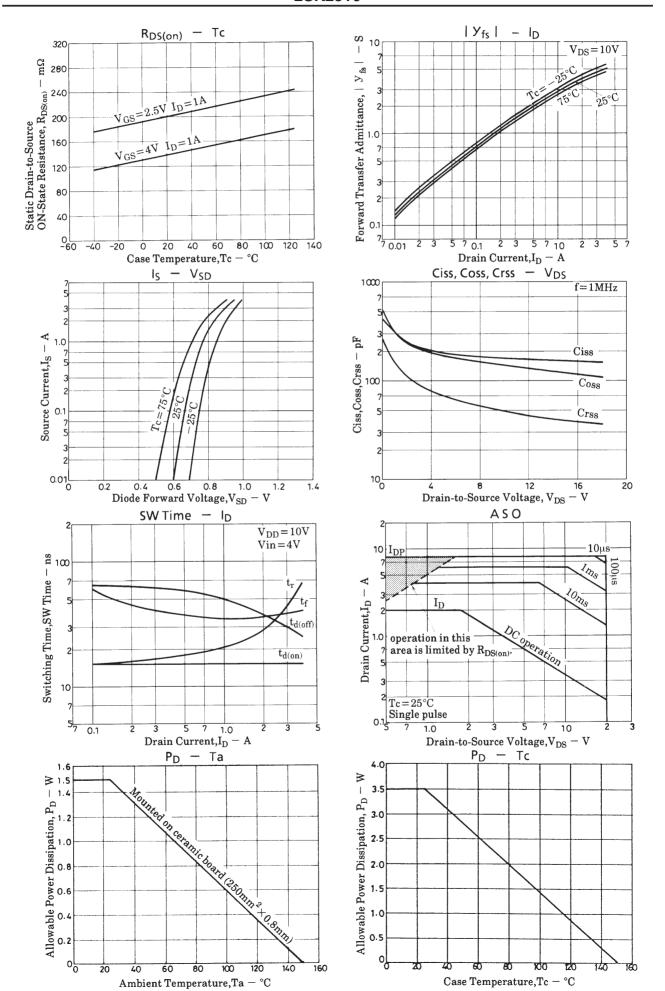
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	td(on)	See specified Test Circuit.		15		ns
Rise Time	tr	"		20		ns
Turn-OFF Delay Time	td(off)	"		50		ns
Fall Time	tf	"		35		ns
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0		1.0		V

Making: KP

Switching Time Test Circuit







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